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APPLICANT(s)
Rainer LOESCH et al.

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U. S. PATENT DOCUMENTS

EXAMINER INITIAL	PATENT NUMBER	PATENT DATE	NAME
LF	5,457,727	October 10, 1995	Peter Frijlink
	5,395,793	March 7, 1995	Sylvain Charbonneau et al.
	5,091,767	February 25, 1992	John C. Bean et al.
	4,088,515	May 9, 1978	A. Eugene Blakeslee et al.
	4,793,872	December 27, 1988	Paul L. Meunier et al.
	5,166,100	November 24, 1992	Arthur C. Gossard et al.
	5,073,893	December 17, 1991	Masahiko Kondou
	5,714,765	February 3, 1998	Richard Noetzel et al.
	4,835,578	May 30, 1989	Tsukuru Ohtoshi et al.

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
				YES	NO
LF	0 332 329	September 13, 1989	Europe	English Document	<input checked="" type="checkbox"/>
LF	38 23 992	January 18, 1990	Germany	English Abstract	<input checked="" type="checkbox"/>

OTHER DOCUMENTS

EXAMINER INITIAL	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
LF	Adomi, K. et al.; "Molecular Beam Epitaxial Growth of GaAs and Other Compound Semiconductors", December 1, 1991, Thin Solid Films, vol. 205, no. 2, pp. 182-212.
	Ando, T. et al.; "Electronic Properties of Two-Dimensional Systems", April 1982, Reviews of Modern Physics, vol. 54, no. 2, p. 437-438.
	Bartels, W.J. et al.; "X-ray Diffraction of Multilayers and Superlattices", November 1, 1986, Acta Crystallographica, vol. A42, part 6, pp. 539-545.
	Bauer, G. et al. (Editors); "Two-Dimensional Systems, Heterostructures, and Superlattices", February 26 - March 2, 1984, Proceedings of the International Winter School, Mauterndorf, Austria. (TOC provided)
	Baumbach, T. et al.; "Characterization of Ga _{1-x} Al _x As/GaAs Superlattices and Thin Single Layers by X-Ray Diffraction", January, 1988, Physica Status Solidi (a); Dept. of Applied Research, vol. 105, no. 1, p. 197-205.
E	Dingle, R.; "Confined Carrier Quantum States in Ultrathin Semiconductor Heterostructures", 1975, Festkörpersprobleme XV: Advances in Solid State Physics, pp. 21-48.

EXAMINER INITIAL		AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
LF		Freyhardt, H.C. (Editor); "Crystals: Growth, Properties, and Applications Growth and Properties" TOC, Springer-Verlag Publishers, 1980, New York.
		Hornstra, J. et al.; "Determination of the Lattice Constant of Epitaxial Layers of III-V Compounds", March 1978, Journal of Crystal Growth, vol. 44, North-Holland Publishing Company, pp. 513-517.
		Jonsson, B. et al.; "Solving the Schrödinger Equation in Arbitrary Quantum-Well Potential Profiles Using the Transfer Matrix Method", November 1990, IEEE Journal of Quantum Electronics, vol. 26, no. 11, pp. 2025-2035.
		Quillec, M.; "Structural Characterization of Superlattices by X-ray Diffraction", Centre National d'Etudes des Telecommunications, Laboratoire de Bagneux, France, pp. 121-135.
		Speriosu, V.S. et al.; "X-ray Rocking Curve Analysis of Superlattices", September 15, 1984, Journal of Applied Physics, vol. 56, no. 6, pp. 1591-1600.
		Takagi, S.; "A Dynamical Theory of Diffraction for a Distorted Crystal", May 1969, Journal of the Physical Society of Japan, vol. 26, no. 5, pp. 1239-1253.
		Tsang, W.T.; "Progress in Chemical Beam Epitaxy", October 1, 1990, Journal of Crystal Growth, vol. 105, nos. 1-4, pp. 1-29.
		Lizunov, V. et al., "Linear and Angular Measurements", 1989 Plenum Publishing Corporation, pp. 283-286.
		van der Sluis, P., "Determination of strain in epitaxial semiconductor layers by high-resolution x-ray diffraction," Phys.D: Appl. Phys. 26 (1993), pp. A188-A191.
		Thompson, P. et al., "Parametric Investigation of Si _{1-x} Ge _x /Si Multiple Quantum Well Growth," J. Appl. Phys. Vol. 33 (1994), pp. 2317-2321.
		Williams, M. et al., "Fabrication of free-standing quantum wells," Appl. Phys. Lett., vol. 61, no. 11, September 14, 1992, p. 1353-1354.
		Yates, M. et al., "Characterization of InP to GaInAs and GaInAs to InP interfaces using tilted cleaved corner TEM," Journal of Crystal Growth 124 (1992), pp. 604-609.
		Sakuma, Y. et al., "Role of interface strain in atomic layer epitaxy growth kinetics of In _x Ga _{1-x} As," Journal of Crystal Growth 114 (1991), pp. 31-37.
		Weimann, G. et al., "Molecular Beam Epitaxy of GaAs and AlGaAs for Optoelectronic Devices and Modulation Doped Heterostructures", Two Dimensional Systems, Heterostructures and Superlattices, 1984, Springer Series in Solid-State Sciences, vol. 53, Springer Publishers, Berlin, pp. 88-99.
		Deckman, H.W. et al; "Microfabrication of molecular scale microstructures," Appl. Phys. Lett., vol. 50, no. 9, March 1987, American Institute of Physics, pp. 504-506.
		"High-Precision Calibration Samples: SEM: MXS „BE" Series - Data Sheet", (Technical Data Sheet), LOT Oriel.
		"Magnification Reference Standards - Data Sheet: SEM: MXS 301CE and MXS 701CE", Moxtek.
		"Magnification Reference Standards - Data Sheet: SEM: MXS 302CE and MXS 702CE", Moxtek.
		"Magnification Reference Standards: SEM: CE Series", Moxtek.
		"Vergrößerungsstandards für die Lichtmikroskopie," Plano Elektronenmikroskopie Technical Data Sheet(s), W. Plannet GmbH.

EXAMINER	DATE CONSIDERED 1/08
EXAMINER: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

